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BOARD DIPLOMA EXAMINATION, (C-14) SEPTEMBER/OCTOBER - 2020 DEEE—FIFTH SEMESTER EXAMINATION

DIGITAL ELECTRONICS

Time : 3 hours]

Total Marks : 80

PART—A

3×10=30

Instructions : (1) Answer all questions.

- (2) Each question carries three marks.
- (3) Answers should be brief and straight to the point and shall not exceed *five* simple sentences.
- **1.** Convert the binary number 10110_2 to decimal number.
- 2. Draw the symbol of EX-OR gate and its truth table.
- **3.** List the characteristics of Digital IC's.
- **4.** Define fan-in and fan-out.
- 5. Define the terms 'power dissipation' and 'propagation delay'.
- 6. Compare the performance of serial and parallel adder.
- 7. Realize half-adder using NAND gates.
- 8. What is race around condition?

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- 9. State the necessity of clock signal.
- **10.** List any three differences between static RAM and dynamic RAM.

PART—B 10×5:

Instructions : (1) Answer any five questions.

- (2) Each question carries **ten** marks.
- (3) Answers should be comprehensive and the criterion for valuation is the content but not the length of the answer.
- **11.** Explain the basic logic gates AND, OR and NOT gates and realize them by using NAND gates.
- **12.** Draw and explain TTL NAND gate with open collector.

13.	(a) Compare TTL, CMOS and ECL logic families.	6
	(b) List any four IC numbers of two input digital IC logic gates.	4
14.	Draw and explain the operation of 1 to 4 demultiplexer.	
15.	(a) Draw the full-adder circuit and explain its operation with truth table.	7
	(b) Realize a half-adder using only NOR gates.	3
16.	Draw and explain asynchronous 3 bit up-down counter.	
17.	Explain the level clocked D and T flip-flops with the help of truth table and circuit diagram.	
18.	(a) Draw and explain the working of basic dynamic MOS RAM cell.	7
	(b) Explain the working principle of NV RAM.	3

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